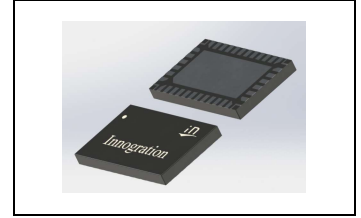




## 5.0-5.2GHz, 100W, 50V GaN fully matched PA Module

### Description

The SMBV5052-100 is a 100-watt, integrated 2-stage Power Amplifier Module, designed for 5G massive MIMO applications, with frequencies from 5 to 5.2 GHz. The module is 50 Ω input and output fully matched, and requires minimal external components. The module offers a much smaller footprint than traditional discrete component solutions, with much less sensitivity for production, housed in 10\*6mm cost effective plastic open cavity package. The module incorporates a Doherty circuit delivering high power added efficiency for the entire module at 16W average power.



**Innegration owns the patents for internal Doherty architecture, and related plastic open cavity.**

• Typical 1 Carrier WCDMA Performance of Doherty Demo (On Innegration fixture with device soldered):

VDS= 50V, Idq_driver=20mA, Idq_main=90mA, Vpeak=-6.1V				
Pout=42dBm				
Freq (MHz)	Ppeak(dBm)	Gain (dB)	EFF (%)	ACPR (dBc)
5000	50.39	28.48	40.09	-27.64
5100	50.22	28.58	39.29	-31.11
5200	50.28	27.84	37.23	-35.05

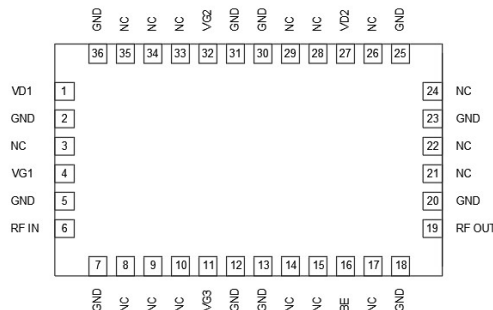
• Notes:

(1) WCDMA signal: 3GPP test model 1; 1 to 64 DPCH; Channel Bandwidth=3.84MHz, PAR =10.5 dB at 0.01 % probability on CCDF.

### Features

- Industry leading RF performance for 5G MIMO AAU, for instance
  - ✓ 32T:320-400 W / 160-200MHz
- Plastic open cavity without molding compound brings advantage compared to molded design
  - ✓ Minimize the risk of high density thermal distribution in fanless system for longer life time
  - ✓ Highly consistent RF performance for yield of volume production
- 50 Ω Input/output matched,
- Integrated Doherty Final and driver Stage
- 6x10 mm Surface Mount Package, full copper flange underneath for grounding and heat dissipation

### Pin Configuration and Description



Pin No.	Symbol	Description
1	VD1	Driver Amplifier, Drain Bias
4	VG1	Driver Amplifier, Gate Bias
6	RF IN	RF Input



11	VG3	Carrier Amplifier, Gate Bias
16	BE	VBW Enhance
19	RF OUT	RF Output
27	VD2	Peaking Amplifier, Drain Bias
32	VG2	Peaking Amplifier, Gate Bias
3,8-10,14-15,17,21,22,24,26,28,29,33-35	NC	No connection
2,5,7,12,13,18,20,23,25,30,31,36	GND	Internal Grounding, recommend connecting to Epad ground
Package Base	GND	DC/RF Ground. Must be soldered to EVB ground plane over array of vias for thermal and RF performance. Solder voids under Pkg Base will result in excessive junction temperatures causing permanent damage.

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain--Source Voltage	$V_{DSS}$	200	Vdc
Gate--Source Voltage	$V_{GS}$	-8 to +0.6	Vdc
Operating Voltage	$V_{DD}$	+55	Vdc
Storage Temperature Range	$T_{stg}$	-65 to +150	°C
Case Operating Temperature	$T_c$	+150	°C
Operating Junction Temperature	$T_j$	+225	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Thermal Resistance@Average Power, Junction to Case Tcase=+85°C, CW Test, Pout=16W,	$R_{\theta JC}$	2.9	°C/W

Notes:

- (1) The thermal resistance is acquired by our company's FEA model, which was calibrated by IR measurement, the value shall be applied to reliability.
- (2) The reference Tcase temperature 85°C is apply on the backside of package.
- (3) If the device soldering onto the 20mil Rogers PCB with 50×Φ0.4mm via hole beneath the package backside and the reference temperature Tcase (85°C) apply on the groundside of the PCB, the total thermal resistance  $R_{\theta JC}$  (TBD)°C/W.
- (4) The power dissipation in the table is overall dissipation which include Carrier PA, Peaking PA and driver PA.

**Table 3. ESD Protection Characteristics**

Test Methodology	Class Voltage
Human Body Model(HBM) (JEDEC Standard JESD-A114)	TBD
Charged Device Model (CDM) (JEDEC Standard JESD22-C101F)	±1000V

**Table 4: Load Mismatch Characteristics (On Test Fixture, 50 ohm system): f = 5.0 GHz**

VSWR 10:1 at P3dB pulse CW Output Power	No Device Degradation
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**Reference Circuit of Test Fixture Assembly Diagram**

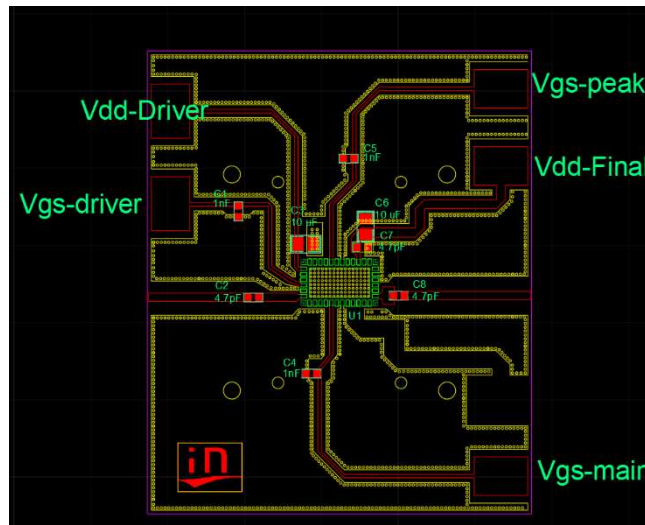


Figure 1. Test Circuit Component Layout

Table 4. Test Circuit Component Designations and Values

Component	Value	Quantity
U1	SMBV5052-100	1
C2、C7、C8	4.7pF	3
C3、C6	10uF/63V	2
C1、C4、C5	1nF	3
PCB	Roger4350B 20mils	

**TYPICAL CHARACTERISTICS**

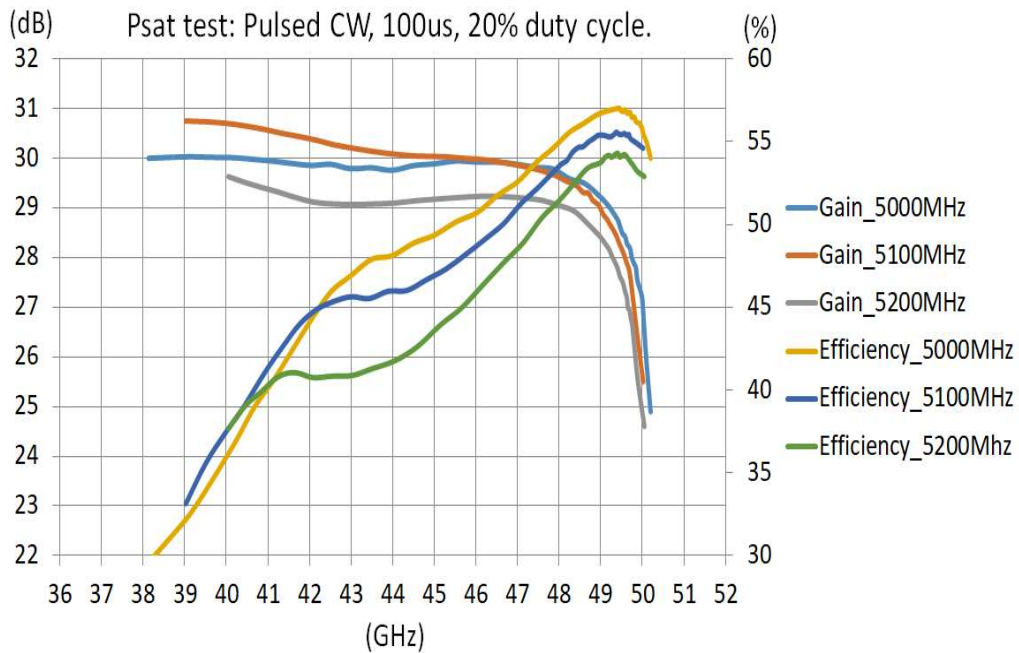


Figure 2. Power Gain and Drain Efficiency as Function of Pulsed CW Output Power

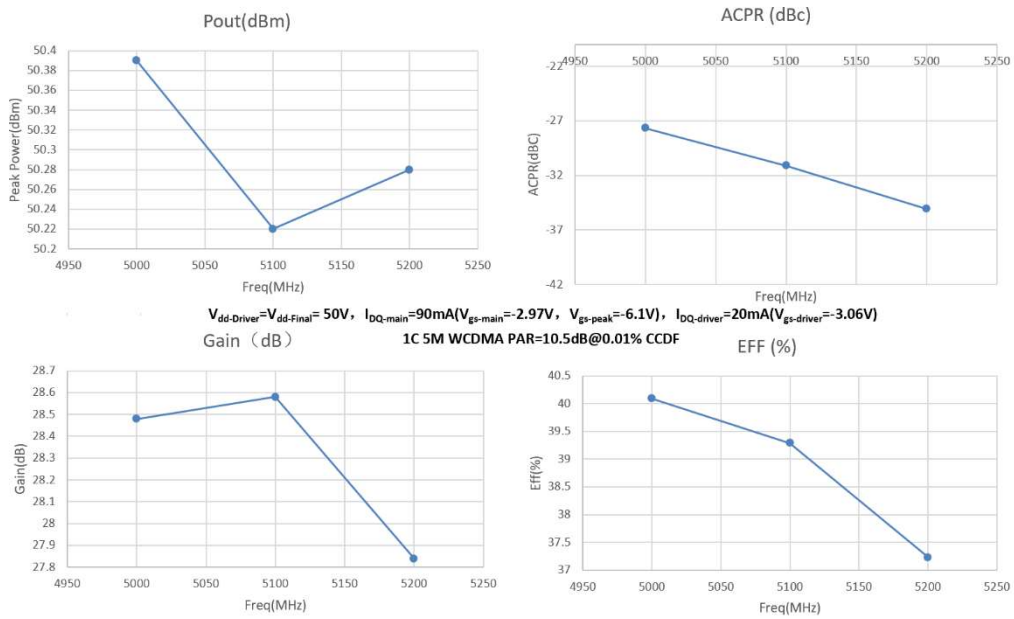


Figure 3. WCDMA performance at Pout=42dBm

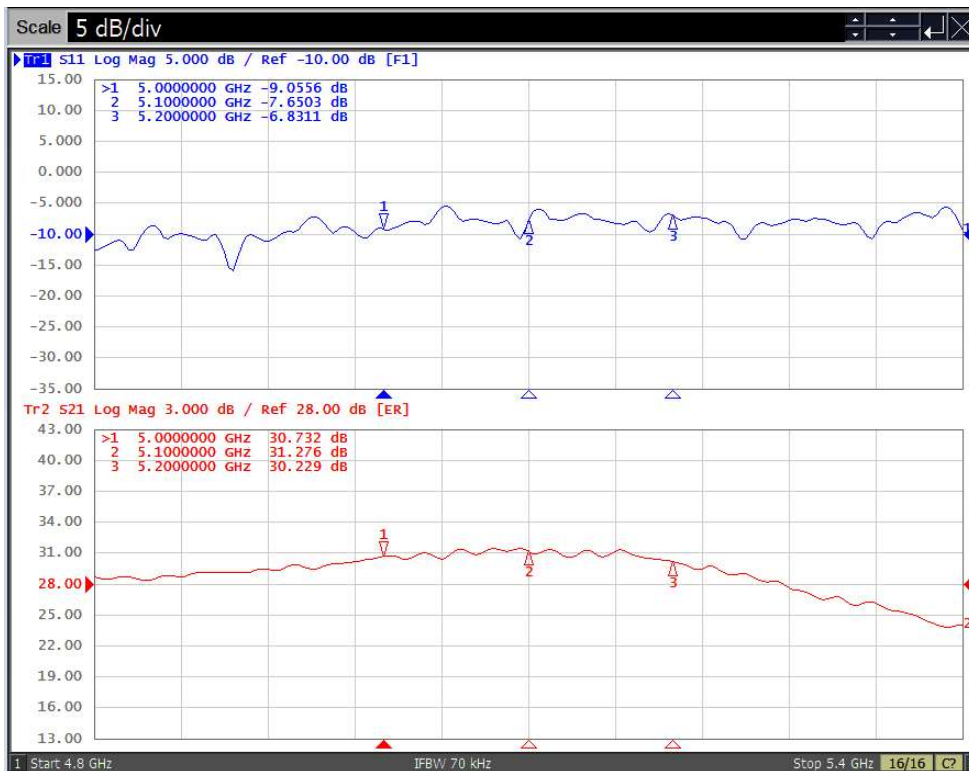
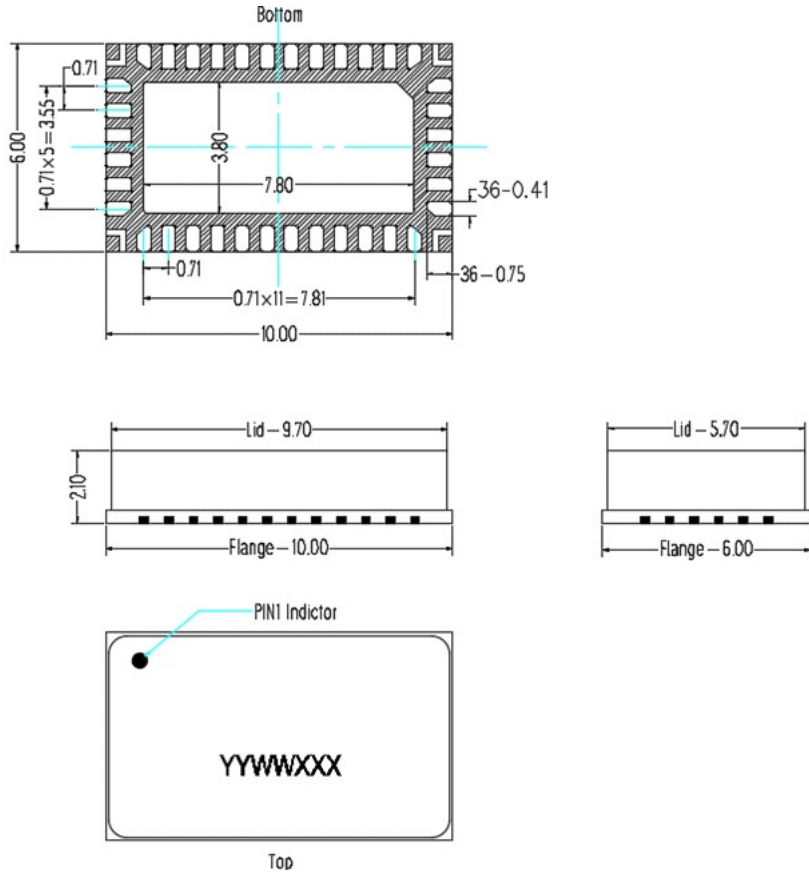


Figure 4. Network analyzer output, S11/S21

## Package Dimensions

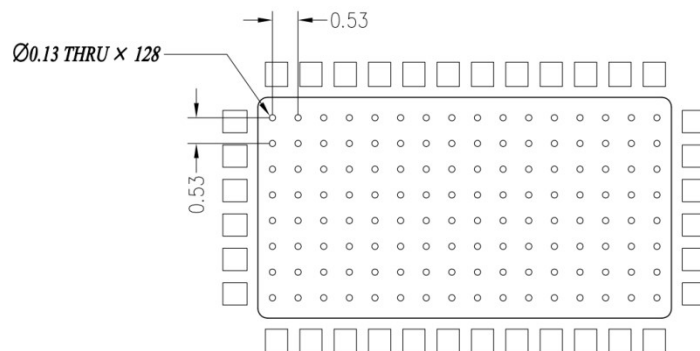
### 10\*6 Plastic Package



#### Notes:

1. All dimensions are in mm;
2. The tolerances unless specified are  $\pm 0.2$ mm.

## Mounting Footprint Pattern



#### Notes:

1. All dimensions are in mm;
2. Vias are required under the backside paddle of this device for proper RF/DC grounding and thermal dissipation. ALL vias are PTH to ground.



## Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2022/3/2	Rev 1.0	Preliminary Datasheet

Application data based on ZYX-22-02

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